



**THE DATASHEET OF
TSM2NB60CH C5G**



N-Channel Power MOSFET

600V, 2A, 4.4Ω

FEATURES

- Advanced planar process
- 100% avalanche tested
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

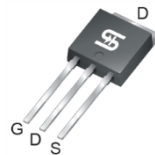
APPLICATION

- Power Supply
- Lighting

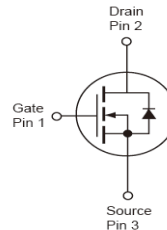
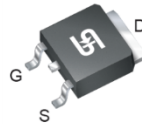
KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
V_{DS}	600	V
$R_{DS(on)}$ (max)	4.4	Ω
Q_g	9.4	nC



TO-251(IPAK)



TO-252(DPAK)



Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (D-PAK) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current ^(Note 1)	$T_C = 25^\circ\text{C}$	I_D	2	A
	$T_C = 100^\circ\text{C}$		1.35	
Pulsed Drain Current ^(Note 2)		I_{DM}	8	A
Single Pulsed Avalanche Energy ^(Note 3)		E_{AS}	55	mJ
Single Pulsed Avalanche Current ^(Note 3)		I_{AS}	2	A
Repetitive Avalanche Energy ^(Note 2)		E_{AR}	4.4	mJ
Peak Diode Recovery dv/dt ^(Note 4)		dv/dt	4.5	V/ns
Total Power Dissipation @ $T_C = 25^\circ\text{C}$		P_{DTOT}	44	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	2.87	$^{\circ}C/W$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	110	$^{\circ}C/W$

Notes: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB in still air

ELECTRICAL SPECIFICATIONS ($T_A = 25^{\circ}C$ unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 5)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2.5	3.6	4.5	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I_{DSS}	--	--	10	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1A$	$R_{DS(ON)}$	--	3.9	4.4	Ω
Forward Transfer Conductance	$V_{DS} = 40V, I_D = 1A$	g_{fs}	--	1.5	--	S
Dynamic (Note 6)						
Total Gate Charge	$V_{DS} = 480V, I_D = 2A,$ $V_{GS} = 10V$	Q_g	--	9.4	--	nC
Gate-Source Charge		Q_{gs}	--	2.2	--	
Gate-Drain Charge		Q_{gd}	--	4.7	--	
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0MHz$	C_{iss}	--	249	--	pF
Output Capacitance		C_{oss}	--	30.7	--	
Reverse Transfer Capacitance		C_{rss}	--	5	--	
Gate Resistance	$F = 1MHz, \text{open drain}$	R_g	--	8.5	--	Ω
Switching (Note 7)						
Turn-On Delay Time	$V_{GS} = 10V, I_D = 2A,$ $V_{DD} = 300V, R_G = 25\Omega$	$t_{d(on)}$	--	9.1	--	ns
Turn-On Rise Time		t_r	--	9.8	--	
Turn-Off Delay Time		$t_{d(off)}$	--	17.4	--	
Turn-Off Fall Time		t_f	--	12.4	--	

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Source-Drain Diode (Note 5)						
Diode Forward Voltage	$I_S = 2\text{A}, V_{GS} = 0\text{V}$	V_{SD}	--	0.9	1.4	V
Reverse Recovery Time	$V_{GS} = 0\text{V}, I_S = 2\text{A},$ $dI_F/dt = 100\text{A}/\mu\text{s}$	t_{rr}	--	490	--	ns
Reverse Recovery Charge		Q_{rr}	--	0.8	--	μC
Source Current	Integral reverse diode in the MOSFET	I_S	--	--	2	A
Source Current (Pulse)		I_{SM}	--	--	8	A

Notes:

1. Current limited by package.
2. Pulse width limited by the maximum junction temperature.
3. $L = 25\text{mH}, I_{AS} = 2\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$.
100% Eas Test Condition: $L = 25\text{mH}, I_{AS} = 1\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
4. $I_{SD} \leq 2\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$.
5. Pulse test: $PW \leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
6. For DESIGN AID ONLY, not subject to production testing.
7. Switching time is essentially independent of operating temperature.

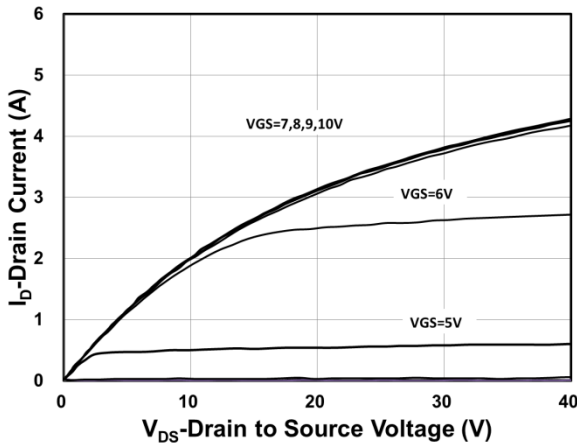
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM2NB60CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM2NB60CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

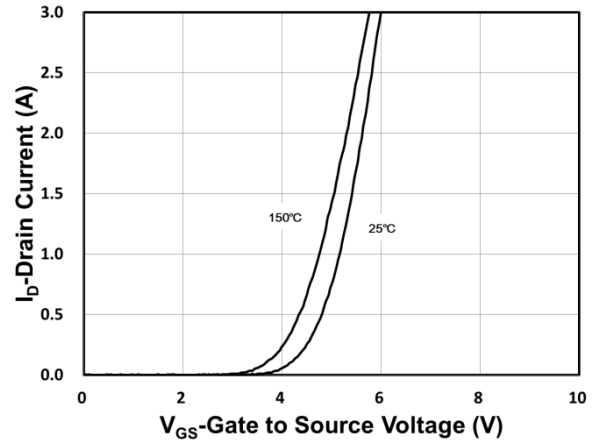
CHARACTERISTICS CURVES

($T_C = 25^\circ\text{C}$ unless otherwise noted)

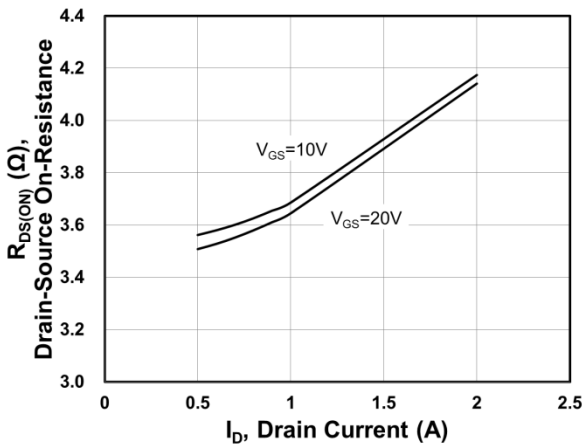
Output Characteristics



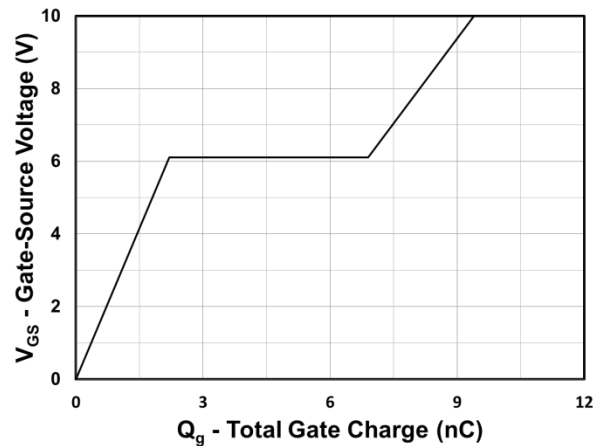
Transfer Characteristics



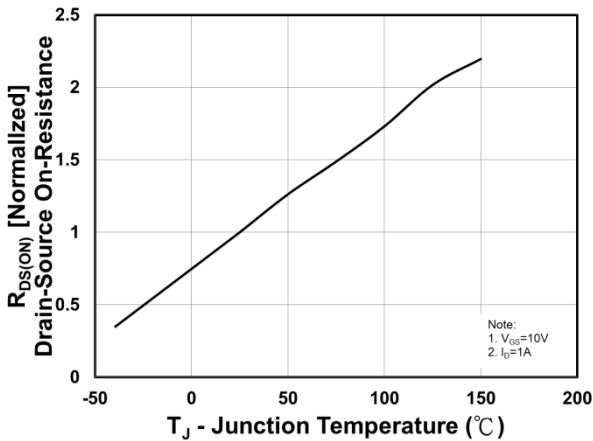
On-Resistance vs. Drain Current



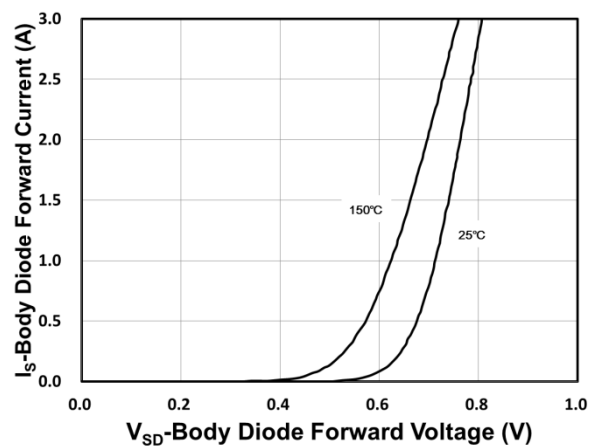
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



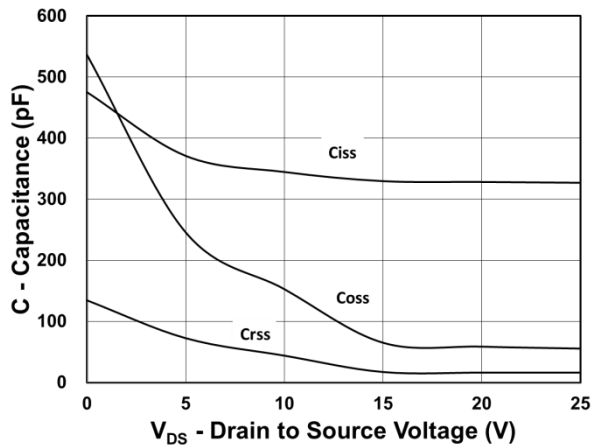
Source-Drain Diode Forward Current vs. Voltage



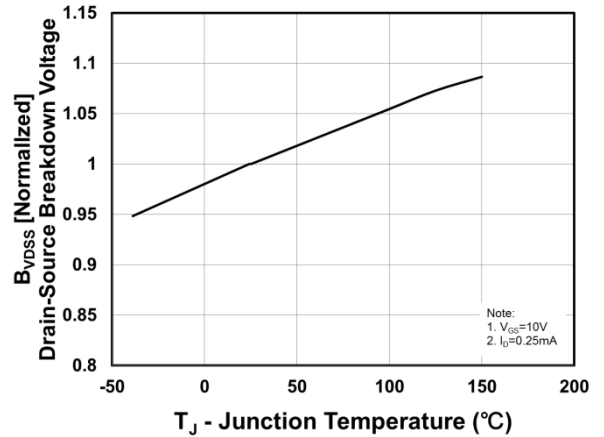
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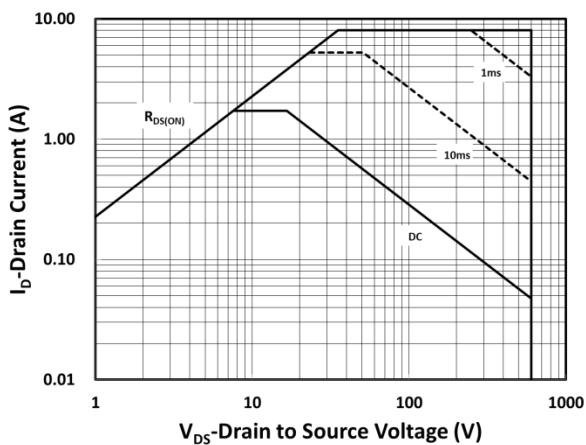
Capacitance vs. Drain-Source Voltage



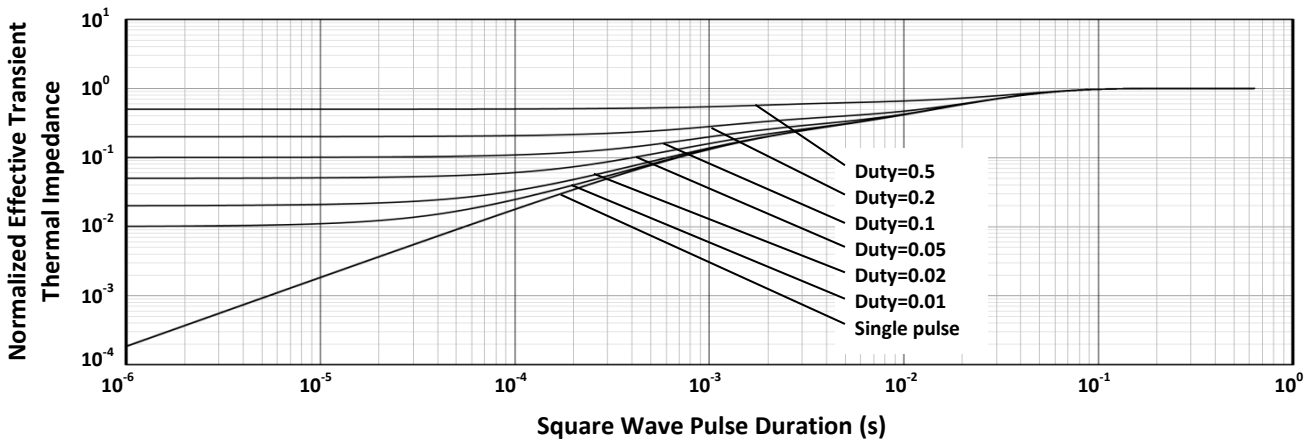
BV_{DSS} vs. Junction Temperature



Maximum Safe Operating Area

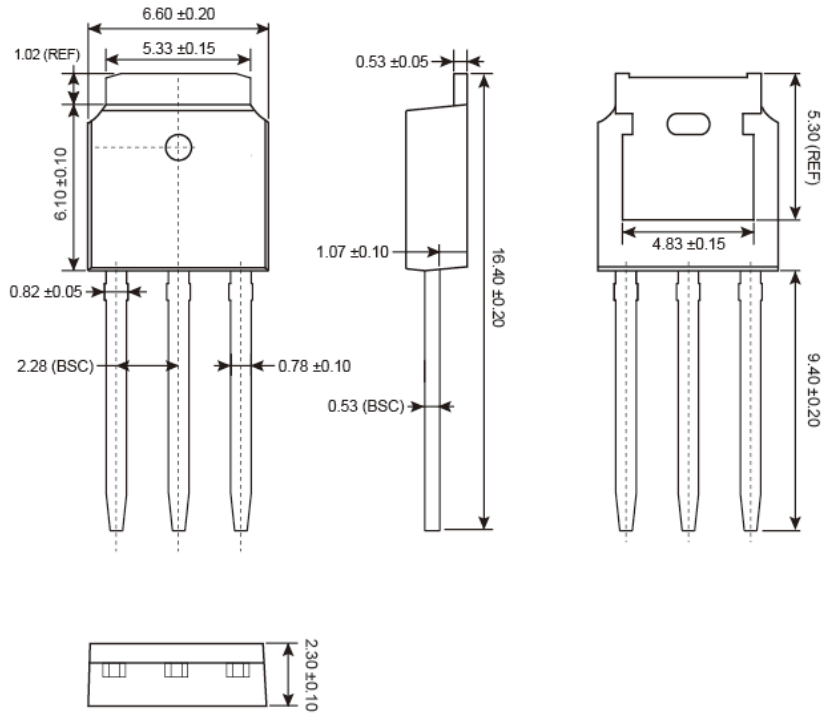


Normalized Thermal Transient Impedance, Junction-to-Case

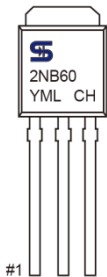


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

TO-251(IPAK)



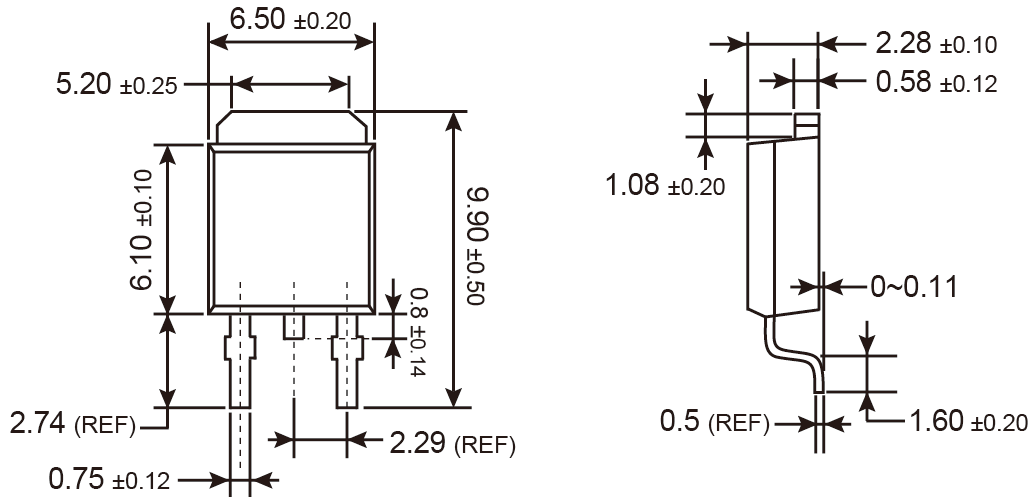
MARKING DIAGRAM



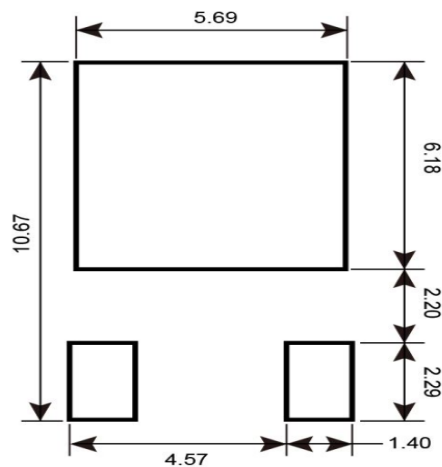
- Y** = Year Code
- M** = Month Code for Halogen Free Product
 - O** =Jan **P** =Feb **Q** =Mar **R** =Apr
 - S** =May **T** =Jun **U** =Jul **V** =Aug
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- L** = Lot Code (1~9, A~Z)

PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

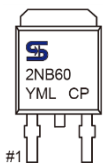
TO-252(DPAK)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



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